



Product Overview

MBRF20100CT: Schottky Power Rectifier, Switch-mode, 20 A, 100 V

For complete documentation, see the data sheet

Product Description

The Schottky Rectifier employs the Schottky Barrier principle in a large metal to silicon power diode. State of the art geometry features epitaxial construction with oxide passivation and metal overlay contact. It is ideally suited for use in low voltage, high frequency switching power supplies, free wheeling diodes and polarity protection diodes.

Features

- Highly Stable Oxide Passivated Junction
- Very Low Forward Voltage Drop
- Matched Dual Die Construction
- High Junction Temperature Capability
- High dv/dt Capability
- Excellent Ability to Withstand Reverse Avalanche Energy Transients
- Guardring for Stress Protection
- Epoxy Meets UL94, V₀ at 1/8"
- Electrically Isolated. No Isolation Hardware Required.
- UL Recognized File #E69369 (Note 1.)

Mechanical Characteristics:

Part Electrical Specifications

Product	Compliance	Status	Configurat ion	V _{RRM} Min (V)	V _F Max (V)	I _{RM} Max (uA)	I _{O(rec)} Max (A)	I _{FSM} Max (A)	t _{rr} Max (ns)	C _j Max (pF)	Package Type
MBRF20100CTG	Pb-free	Active	Common Cathode	100	0.95	150	20	150			TO-220 FULLPAK- 3

For more information please contact your local sales support at www.onsemi.com

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